

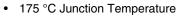


N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
150	0.095 at V _{GS} = 10 V	15	
150	0.100 at V _{GS} = 6 V	15	

FEATURES

• TrenchFET® Power MOSFETS



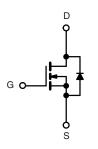


100 % R_g Tested

Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

· Primary Side Switch



N-Channel MOSFET

TO-252	
G D S	Drain Connected to Tab
Top View	

Ordering Information: SUD15N15-95-E3 (Lead (Pb) free)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	150	.,	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Dusin Comment (T. 177 °C)b	T _C = 25 °C	1	15		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	I _D	8.7		
Pulsed Drain Current		I _{DM}	25	Α	
Continuous Source Current (Diode Conduction)		I _S	15		
Avalanche Current		I _{AR}	15		
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	11.3	mJ	
Mayimum Dayyar Dissination	T _C = 25 °C	P _D	62 ^b	W	
Maximum Power Dissipation	T _A = 25 °C	'D	2.7 ^a		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	16	20	°C/W
Junction-to-Ambient*	Steady State		45	55	
Junction-to-Case		R _{thJC}	2	2.4	

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.

SUD15N15-95

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					<u> </u>		
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 120 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	25			Α	
		V _{GS} = 10 V, I _D = 15 A		0.077	0.095		
D : 0	D	V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.190	Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.250		
		V _{GS} = 6 V, I _D = 10 A		0.081	0.100		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		25		S	
Dynamic ^a							
Input Capacitance	C _{iss}			900		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		115			
Reverse Transfer Capacitance	C _{rss}			70			
Total Gate Charge ^c	Q_g			20	25		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		5.5		nC	
Gate-Drain Charge ^c	Q_{gd}			7			
Gate Resistance	R _g		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			8	12		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		35	55	no	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		17	25	ns	
Fall Time ^c	t _f			30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	C = 25 °C)		_			
Pulsed Current	I _{SM}				25	Α	
Diode Forward Voltage ^b	V _{SD}	I _F = 15 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 15 A, dl/dt = 100 A/μs		55	85	ns	

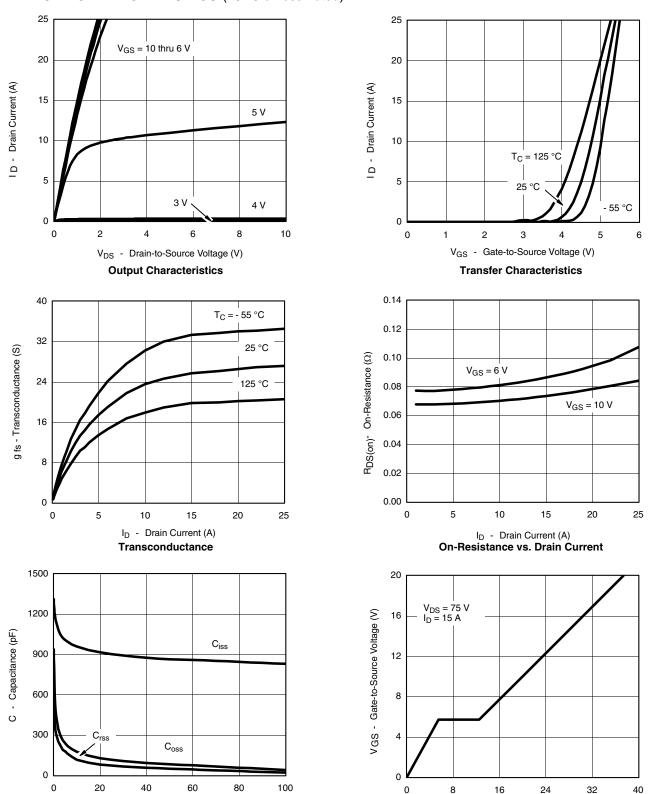
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)

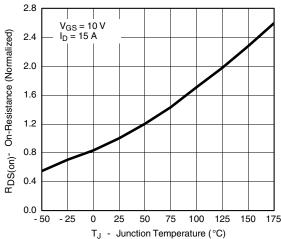


Qg - Total Gate Charge (nC)

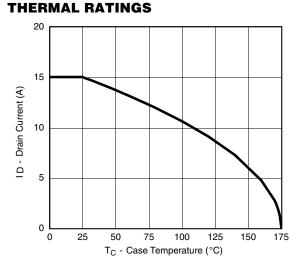
Gate Charge

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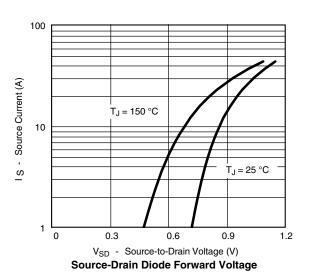
TYPICAL CHARACTERISTICS (25 °C unless noted)

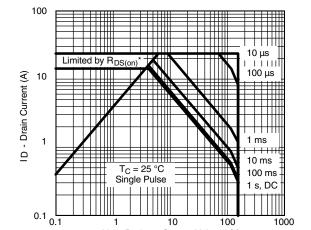


On-Resistance vs. Junction Temperature

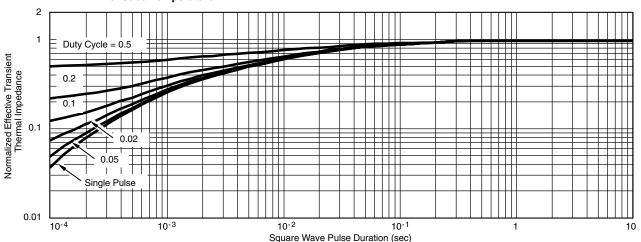


Maximum Avalanche Drain Current vs. Case Temperature





V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified Safe Operating Area



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and

reliability data, see www.vishay.com/ppg?71641.

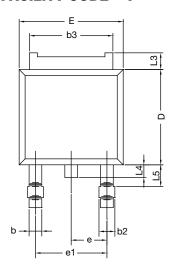
Normalized Thermal Transient Impedance, Junction-to-Case

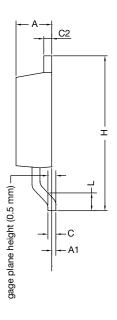
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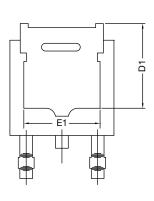


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







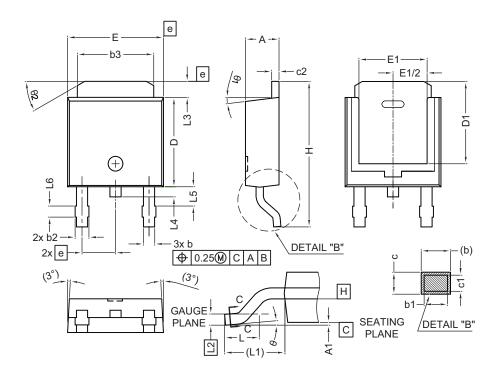
	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
Е	6.35	6.73	
E1	4.32	=	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	-	1.02	
L5	1.01	1.52	

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	=	
Е	6.35	6.73	
E1	4.32	=	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS	
DIM.	MIN.	MAX.
L	1.50	1.78
L1	2.74	ref.
L2	0.51	BSC
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

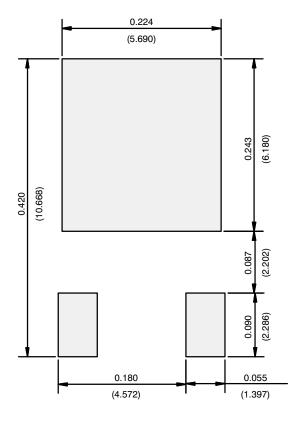
- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- · Radius on terminal is optional

ECN: E19-0649-Rev. Q, 16-Dec-2019

DWG: 5347



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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